

VDS

 I_D

R_{DS(ON)TYP}

N-Channel Super Junction Power MOSFET III

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

- •New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- ●100% Avalanche Tested
- ROHS compliant

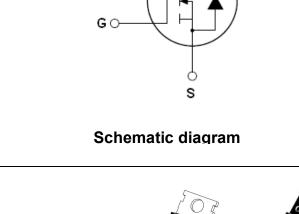
Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

Package Marking And Ordering Information

| Device | Device Package | Marking | |
|------------|----------------|------------|--|
| NCE65T900D | TO-263 | NCE65T900D | |
| NCE65T900 | TO-220 | NCE65T900 | |
| NCE65T900F | TO-220F | NCE65T900F | |

Table 1 Absolute Maximum Ratings (T_=25°C)



650

750

5

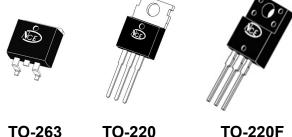
V

mΩ

А

D

С



TO-263

TO-220F

| Parameter | Symbol | NCE65T900 NCE65T900D NCE65T900D | | Unit |
|---|---------------------|---------------------------------------|------|------|
| Drain-Source Voltage (VGs=0V) | Vds | 650 | | V |
| Gate-Source Voltage (VDs=0V) AC (f>1 Hz) | Vgs | ±30 | | V |
| Continuous Drain Current at Tc=25°C | I _{D (DC)} | 5 | 5* | А |
| Continuous Drain Current at Tc=100°C | I _{D (DC)} | 3 | 3* | А |
| Pulsed drain current (Note 1) | DM (pluse) | 20 | 20* | А |
| Maximum Power Dissipation(Tc=25°C) | PD | 46 | 29 | W |
| Derate above 25°C | | 0.37 | 0.23 | W/°C |
| Single pulse avalanche energy (Note2) | Eas | 52 | | mJ |
| Avalanche current ^(Note 1) | I _{AR} | 0.9 | | А |
| Repetitive Avalanche energy , t_{AR} limited by T_{jmax} (Note 1) | E _{AR} | 0.14 | | mJ |



NCE65T900D, NCE65T900, NCE65T900F

| Parameter | Symbol | NCE65T900 NCE65T900D | NCE65T900F | Unit |
|---|----------------------------------|-------------------------|------------|------|
| Drain Source voltage slope, $V_{DS} \leqslant 480 V$, | dv/dt | 50 | | V/ns |
| Reverse diode dv/dt, $V_{DS} \leqslant 480 V, I_{SD} < I_D$ | dv/dt | 1 | 5 | V/ns |
| Operating Junction and Storage Temperature Range | T _J ,T _{STG} | -55 | +150 | °C |

* limited by maximum junction temperature

Table 2. Thermal Characteristic

| Parameter | Symbol | NCE65T900 NCE65T900D | NCE65T900F | Unit |
|---|-------------------|-------------------------|------------|-------|
| Thermal Resistance, Junction-to-Case (Maximum) | R _{thJC} | 2.72 | 4.3 | °C /W |
| Thermal Resistance, Junction-to-Ambient (Maximum) | R _{thJA} | 62 | 80 | °C /W |

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|---|---------------------|---|-----|------|------|------|
| On/off states | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250µA | 650 | | | V |
| Zero Gate Voltage Drain Current(Tc=25°C) | I _{DSS} | V _{DS} =650V,V _{GS} =0V | | | 1 | μA |
| Zero Gate Voltage Drain Current(Tc=125°C) | I _{DSS} | V _{DS} =650V,V _{GS} =0V | | | 50 | μA |
| Gate-Body Leakage Current | I _{GSS} | V_{GS} =±20V, V_{DS} =0V | | | ±100 | nA |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} ,I _D =250µA | 3 | | 4 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =2.5A | | 750 | 900 | mΩ |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C _{lss} | | | 370 | | pF |
| Output Capacitance | C _{oss} | - V _{DS} =50V,V _{GS} =0V, - F=1.0MHz | | 25 | | pF |
| Reverse Transfer Capacitance | C _{rss} | | | 0.5 | | pF |
| Total Gate Charge | Qg | | | 10.5 | 15 | nC |
| Gate-Source Charge | Q _{gs} | - V _{DS} =480V,I _D =5A, - V _{GS} =10V | | 2.6 | | nC |
| Gate-Drain Charge | Q _{gd} | - V _{GS} =10V | | 5.3 | | nC |
| Switching times | | | | | | |
| Turn-on Delay Time | t _{d(on)} | | | 7 | | nS |
| Turn-on Rise Time | tr | V _{DD} =380V,I _D =3A, | | 3 | | nS |
| Turn-Off Delay Time | t _{d(off)} | R _G =5Ω,V _{GS} =10V | | 52 | 62 | nS |
| Turn-Off Fall Time | t _f | | | 10 | 16 | nS |
| Source- Drain Diode Characteristics | | | | | | |
| Source-drain current(Body Diode) | I _{SD} | – T _C =25°C | | | 5 | А |
| Pulsed Source-drain current(Body Diode) | I _{SDM} | - 1 _C -25 C | | | 20 | А |
| Forward on voltage | V _{SD} | Tj=25°C,I _{SD} =5A,V _{GS} =0V | | 0.9 | 1.2 | V |
| Reverse Recovery Time | trr | | | 210 | | nS |
| Reverse Recovery Charge | Qrr | Tj=25°C,I _F =2.5A,di/dt=100A/μs | | 0.66 | | uC |
| Peak reverse recovery current | Irrm | | | 6.5 | | А |

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25 $^\circ\!\mathrm{C},VDD$ =50V,VG=10V, R_G=25 Ω



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area for TO-220, TO-263

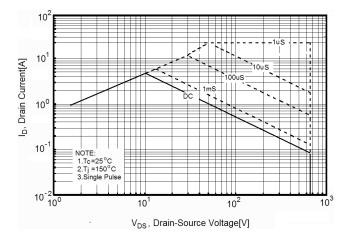


Figure3. Source-Drain Diode Forward Voltage

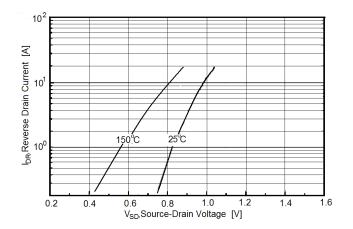


Figure5. Transfer characteristics

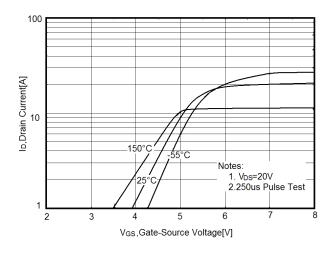


Figure 2. Safe operating area for TO-220F

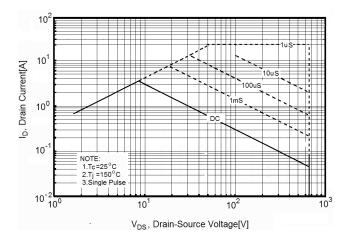


Figure4. Output characteristics

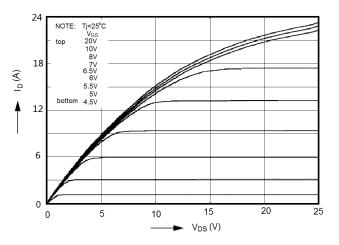


Figure6. Static drain-source on resistance

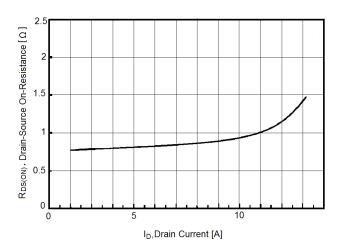




Figure7. R_{DS(ON)} vs Junction Temperature

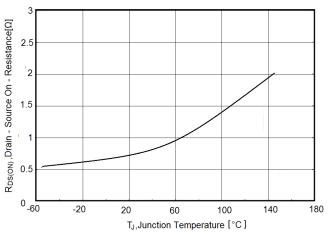


Figure9. Maximum I_D vs Junction Temperature

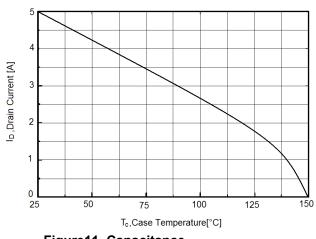


Figure11. Capacitance

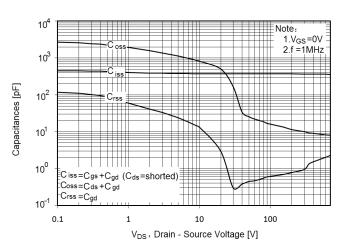


Figure8. BV_{DSS} vs Junction Temperature

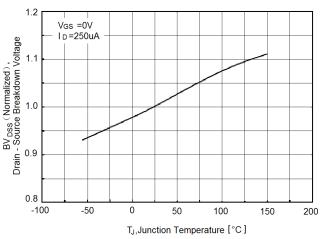


Figure10. Gate charge waveforms

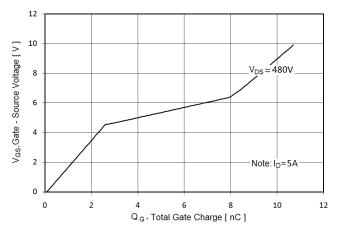
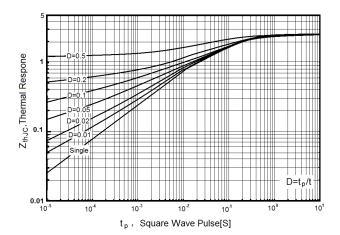


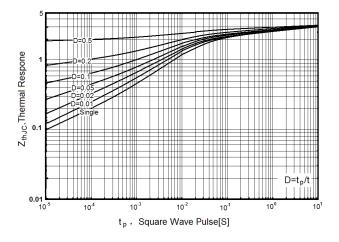
Figure12. Transient Thermal Impedance



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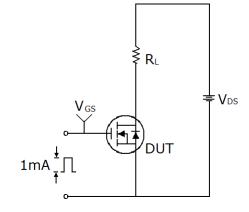
Figure13. Transient Thermal Impedance for TO-220F

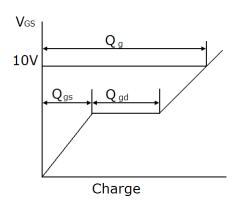




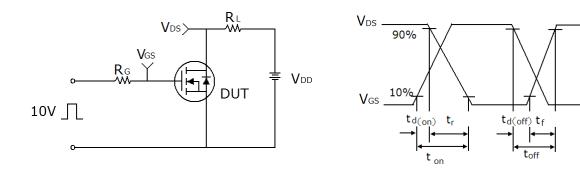
Test circuit

1) Gate charge test circuit & Waveform

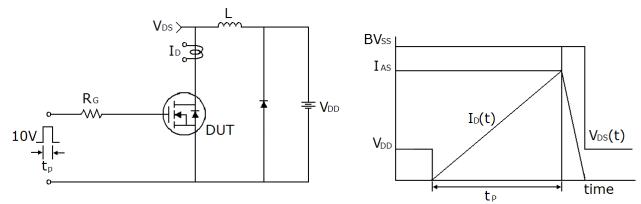




2) Switch Time Test Circuit:



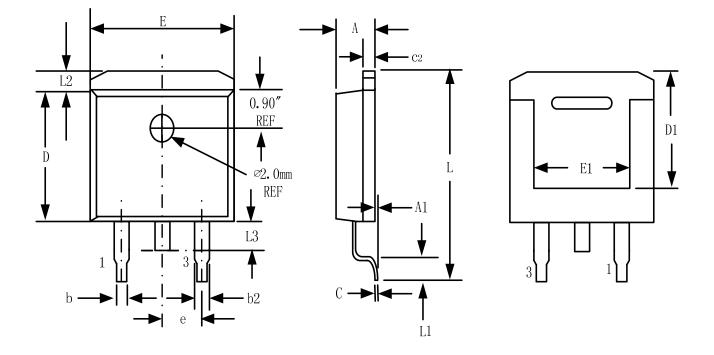
3) Unclamped Inductive Switching Test Circuit & Waveforms



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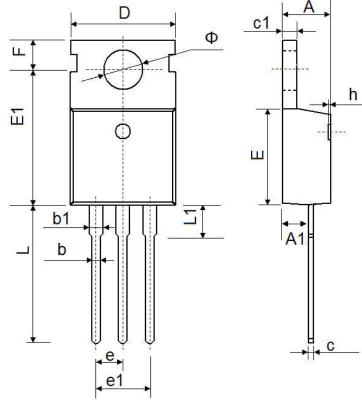
TO-263-3L Package Information

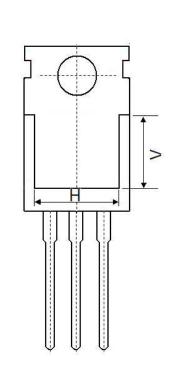


| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| Symbol | Min. | Max. | Min. | Max. | |
| A | 4.32 | 4.57 | 0.170 | 0.180 | |
| A1 | - | 0.25 | | 0.010 | |
| b | 0.71 | 0.94 | 0.028 | 0.037 | |
| b2 | 1.15 | 1.40 | 0.045 | 0.055 | |
| С | 0.46 | 0.61 | 0.018 | 0.024 | |
| c2 | 1.22 | 1.40 | 0.048 | 0.055 | |
| D | 8.89 | 9.40 | 0.350 | 0.370 | |
| D1 | 8.01 | 8.23 | 0.315 | 0.324 | |
| E | 10.04 | 10.28 | 0.395 | 0.405 | |
| E1 | 7.88 | 8.08 | 0.310 | 0.318 | |
| е | 2.54 | 4 BSC | 0.100 | BSC | |
| L | 14.73 | 15.75 | 0.580 | 0.620 | |
| L1 | 2.29 | 2.79 | 0.090 | 0.110 | |
| L2 | 1.15 | 1.39 | 0.045 | 0.055 | |
| L3 | 1.27 | 1.77 | 0.050 | 0.070 | |



TO-220-3L-C Package Information

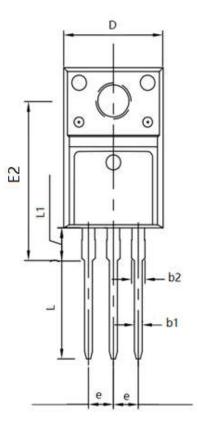


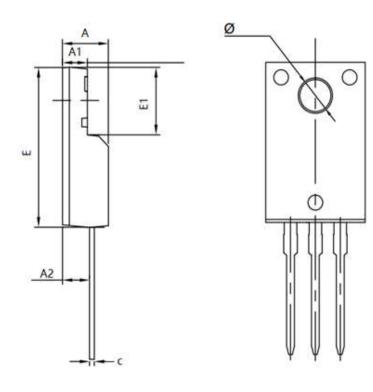


| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| | Min. | Max. | Min. | Max. | |
| А | 4.400 | 4.600 | 0.173 | 0.181 | |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| b | 0.710 | 0.910 | 0.028 | 0.036 | |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 | |
| С | 0.330 | 0.650 | 0.013 | 0.026 | |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 | |
| D | 9.910 | 10.250 | 0.390 | 0.404 | |
| E | 8.9500 | 9.750 | 0.352 | 0.384 | |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 | |
| е | 2.540 TYP. | | 0.100 TYP. | | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 | |
| F | 2.650 | 2.950 | 0.104 | 0.116 | |
| Н | 7.900 | 8.100 | 0.311 | 0.319 | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |
| L | 12.900 | 13.400 | 0.508 | 0.528 | |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 | |
| V | 7.500 REF. | | 0.295 REF. | | |
| Ф | 3.400 | 3.800 | 0.134 | 0.150 | |



TO-220F Package Information





| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| | Min. | Max. | Min. | Max. | |
| А | 4.500 | 4.900 | 0.177 | 0.193 | |
| A1 | 2.340 | 2.740 | 0.092 | 0.108 | |
| A2 | 2.560 | 2.960 | 0.101 | 0.117 | |
| b1 | 0.700 | 0.900 | 0.028 | 0.035 | |
| b2 | 1.180 | 1.580 | 0.046 | 0.062 | |
| С | 0.400 | 0.600 | 0.016 | 0.024 | |
| D | 9.960 | 10.360 | 0.392 | 0.408 | |
| E | 15.670 | 15.970 | 0.617 | 0.629 | |
| E1 | 6.500 | 6.900 | 0.256 | 0.272 | |
| E2 | 15.500 | 16.100 | 0.610 | 0.634 | |
| е | 2.54 | 2.540 TYP | |) TYP | |
| Φ | 3.080 | 3.280 | 0.121 | 0.129 | |
| L | 12.640 | 13.240 | 0.498 | 0.521 | |
| L1 | 3.030 | 3.430 | 0.119 | 0.135 | |



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